

# Breakdown studies with the Pulsed DC Systems: Optimizing the pulsing parameters & Results from He irradiation



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# Contents

1. **Motivation:** DC experiments to understand BD behaviour
2. **Pulsed DC Systems:** Small gap breakdown generation with Cu electrodes
3. **Optimizing the pulsing parameters:** Effect of pauses between pulses
4. **He irradiation:** Trying to nucleate BDs with subsurface voids
5. **Conclusions**

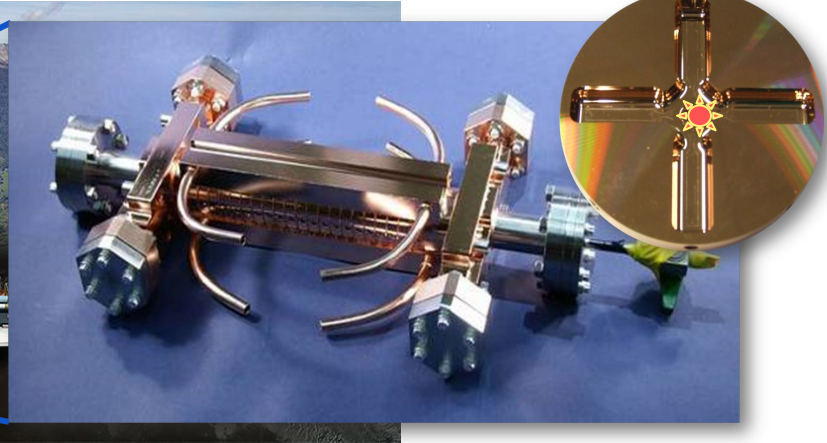
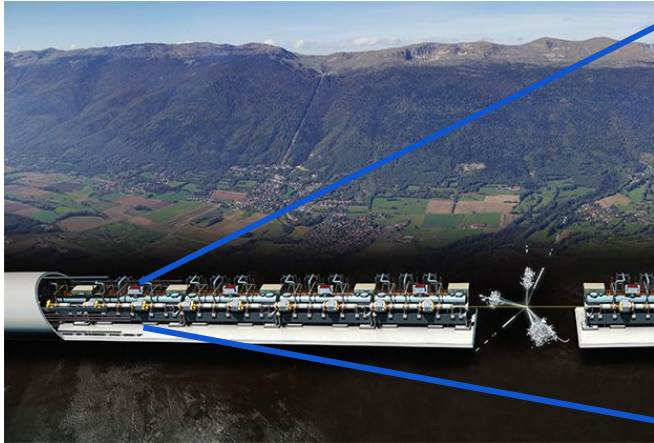
# Motivation

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# Breakdowns limit the efficiency of the Compact Linear Collider



Photo: CERN



- Colliding electrons and positrons
- Linear accelerator built in stages
  - 380 GeV / 11 km x 2  $\Rightarrow$  70 MV/m
  - ...
  - 3 TeV / 50 km x 2  $\Rightarrow$  120 MV/m

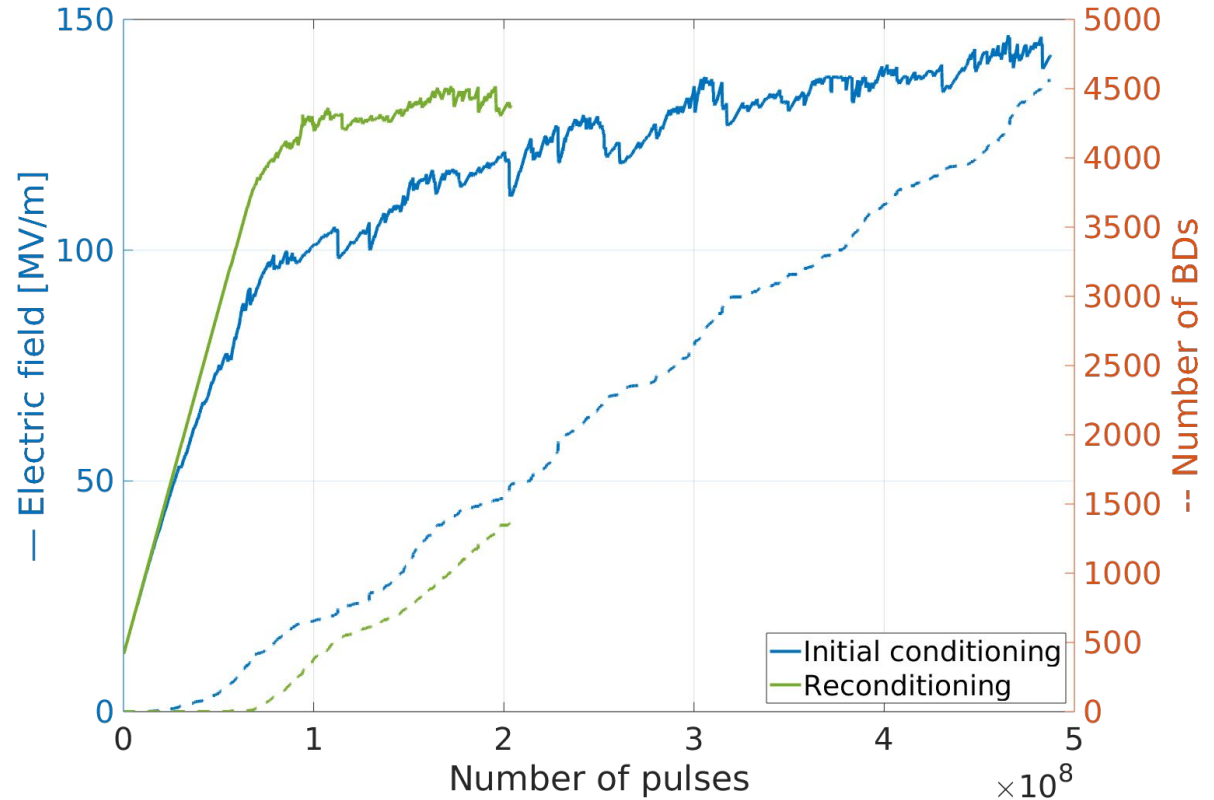
- Copper accelerating structures in vacuum @ room temperature

$\Rightarrow$  **Breakdowns**



# Copper requires conditioning to endure breakdowns

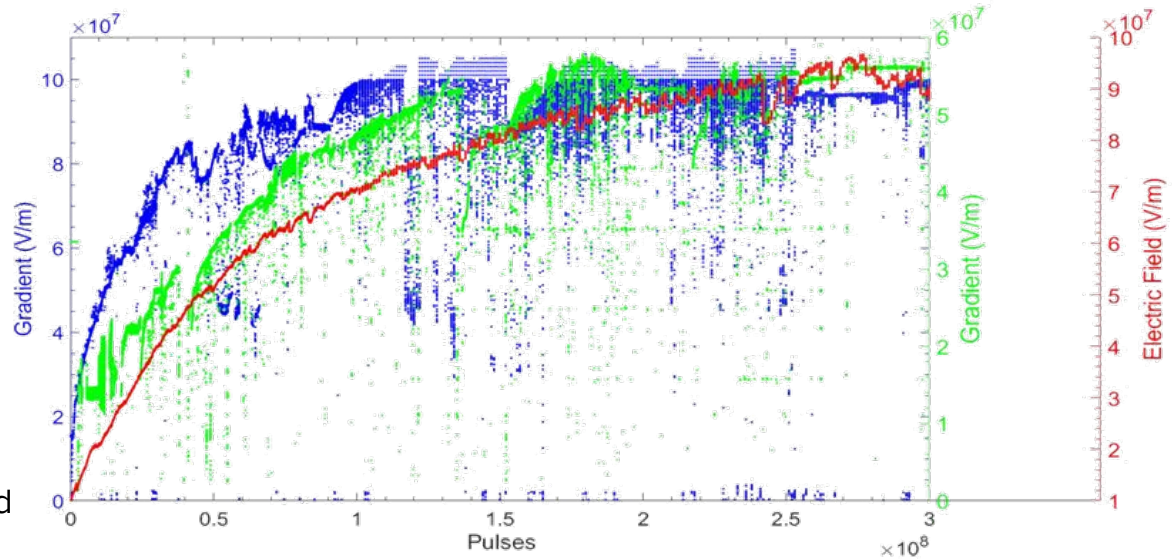
- Pristine electrodes vulnerable to BDs already at small fields
- After  $\sim 5 \times 10^8$  pulses &  $\sim 5000$  BDs, BD field can be 5 times higher
- Long and short term conditioning?





# Faster conditioning with DC compared to RF

- Conditioning curves similar between Sbox, Xbox3 and Pulsed DC LES
- Huge difference in time scales
  - Sbox @ 25 Hz: 4 months
  - Xbox @ 200 Hz: 2 months
  - Pulsed DC LES @ 2 kHz: 3.5 days
- Pulsed DC System much smaller and simpler to operate compared to Xboxes
  - Allows focus on the BDs only



Measurements:  
Lee Millar and  
Iaroslava Profatilova

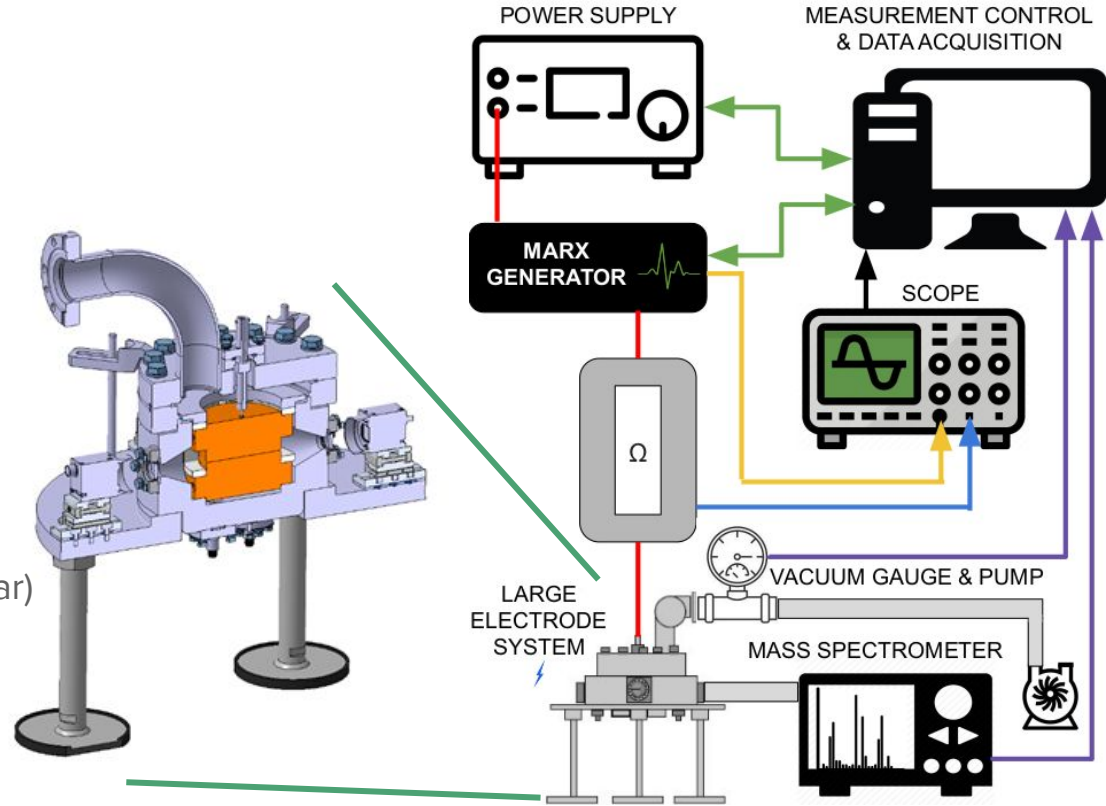
# Experimental setup: Pulsed DC Systems

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# Pulsed DC Systems

- Similar systems at CERN and in Helsinki, also one in Uppsala
- Cu electrodes
  - 40-60 mm contact diameter
  - 40-60  $\mu\text{m}$  gap
- Short DC pulses
  - Electric fields up to 150 MV/m
  - 1  $\mu\text{s}$  pulses @ 2 kHz
  - (near) Ultra High Vacuum ( $< 10^{-7}$  mbar)
  - Room temperature
- $\sim 1000$  BDs /  $10^8$  pulses per day

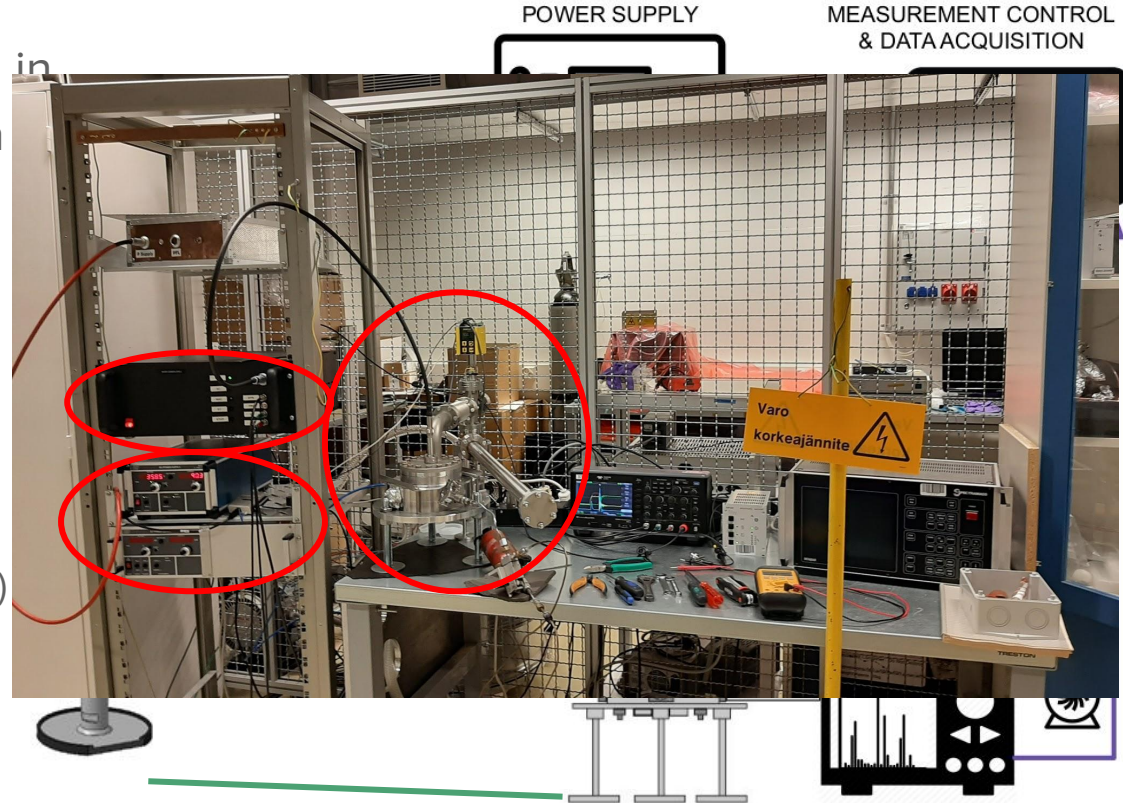






# Pulsed DC systems

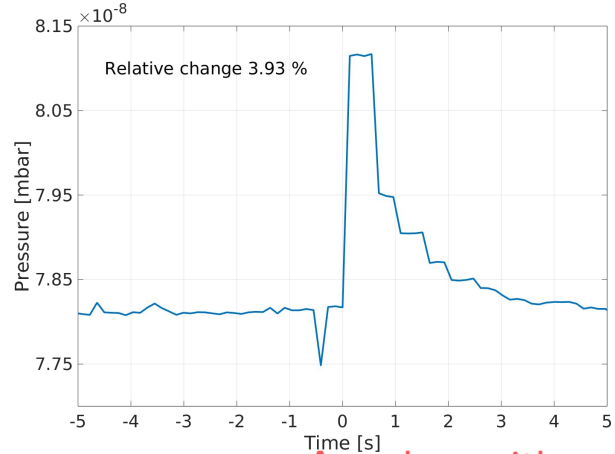
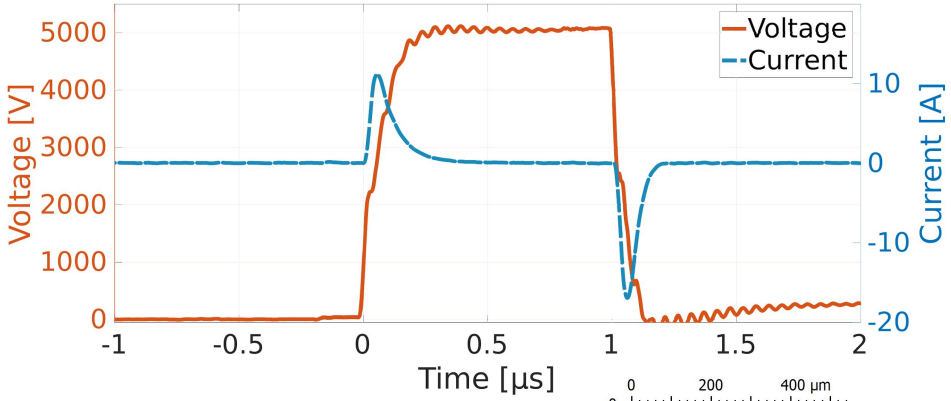
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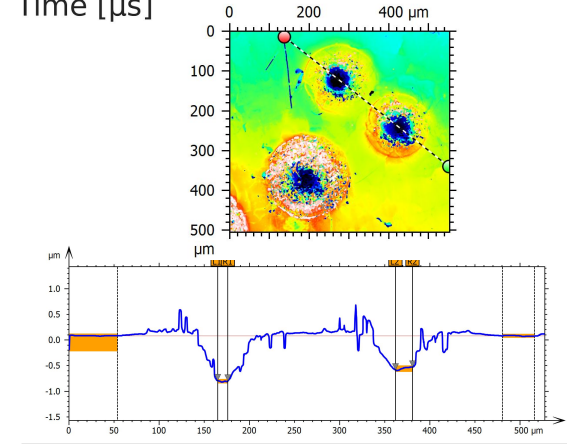
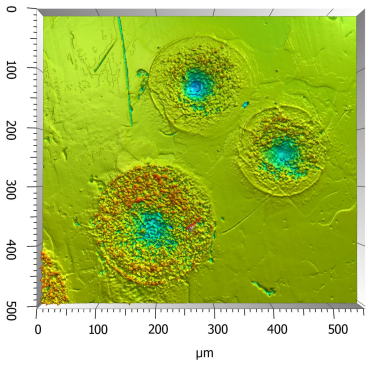
# Pulse shapes: BDs are detected from current peaks



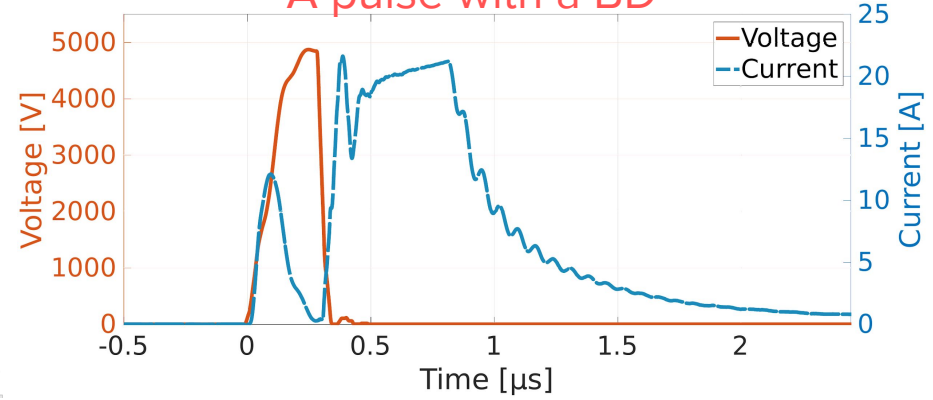
## Normal pulse without a BD



Breakdowns are also seen as pressure spikes



## A pulse with a BD



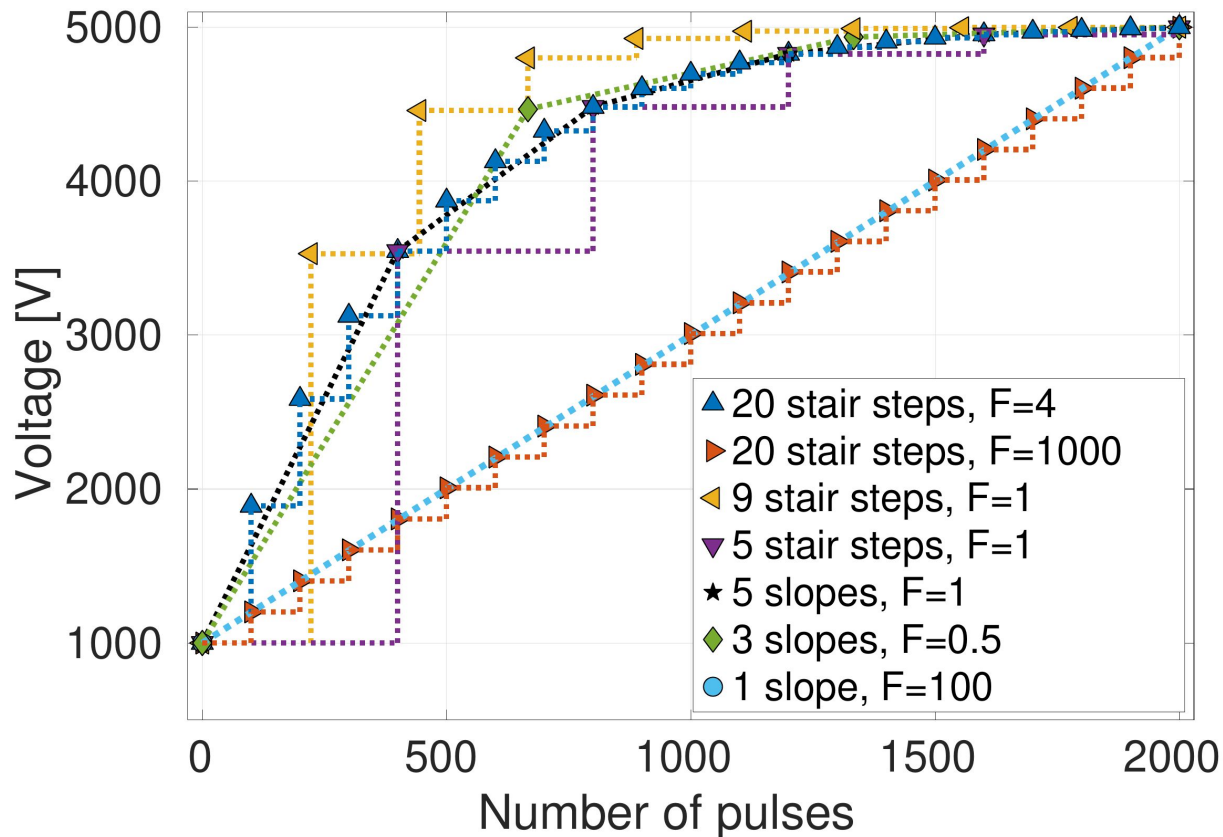
# Optimizing the pulsing parameters

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# Voltage recovery after BDs - “ramping”



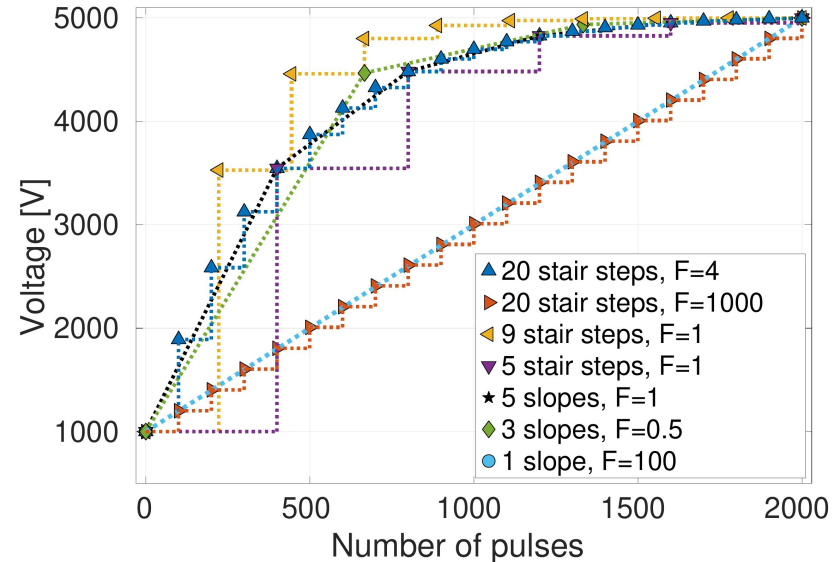
- “Ultra-short term conditioning”
- Voltage is ramped up from one fifth to the target value over 2000 pulses
- But the ramping itself increases BD probability
- Why? And how to ramp up causing minimum secondary BDs





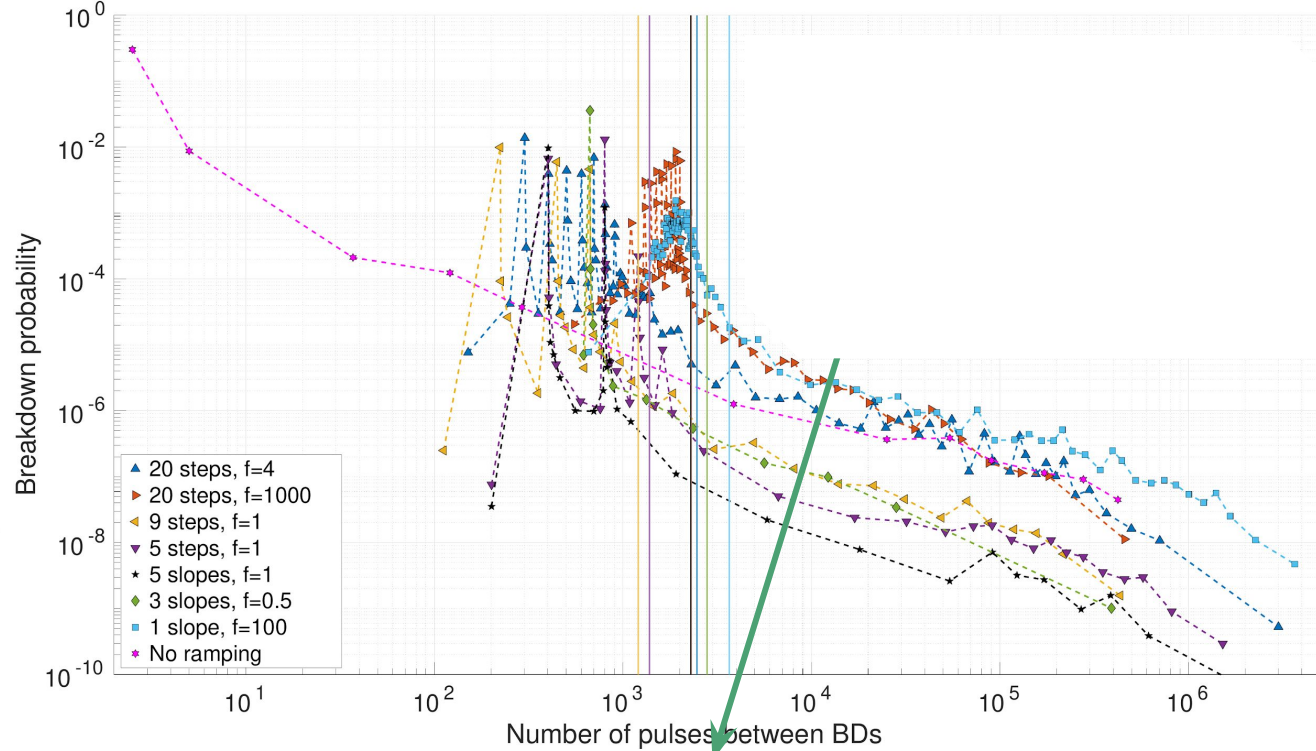
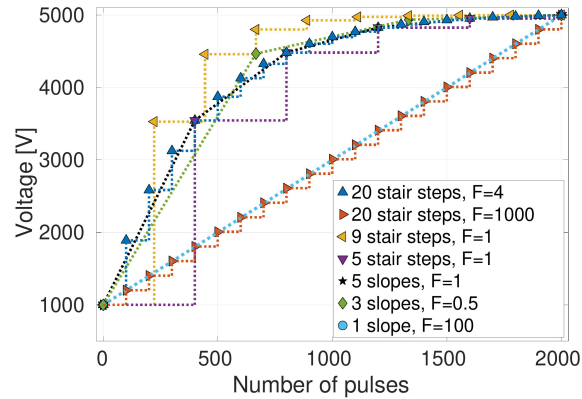
# Ramping scenario comparison

	Scenario	Total BDR	Secondary BD %	BD serie length
▲	Steps, 20 steps, F=4	1.78E-05	70	3.3 ± 0.1
▶	Steps, 20 steps, F=1000	7.68E-05	82	4.3 ± 0.2
▼	Steps, 9 steps, F=1	8.18E-05	88	7.4 ± 0.6
◆	Steps, 5 steps, F=1	2.05E-05	84	5.3 ± 0.4
★	Slopes, 5 slopes, F=1	3.37E-05	90	10.6 ± 0.8
◆	Slopes, 3 slopes, F=0.5	2.98E-04	96	20.4 ± 1.1
●	Slopes, 1 slope, F=100	5.86E-06	67	3.1 ± 0.1
□	No ramping	9.60E-05	94	15.3 ± 1.3





# Ramping affects BD probability



$$PDF = A \exp(\alpha n) + B \exp(\beta n)$$

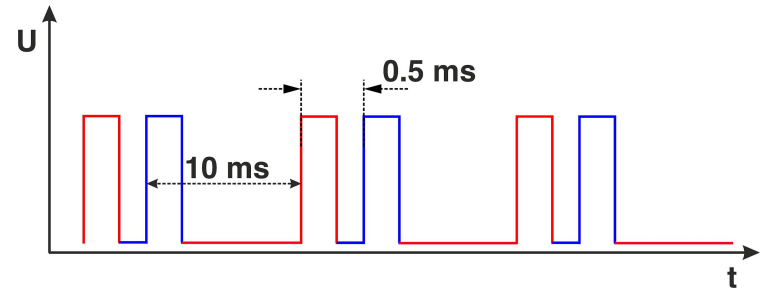


# Effect of the repetition rate

- What is the optimal pulsing frequency?
- Marx generator allows repetition rates up to 6 kHz

## 3 experiments:

1. Variable repetition rate from 10 Hz to 6000 Hz
2. Swap between two repetition rates (100 Hz vs 2000 Hz)
3. Burst mode: change repetition rate after every pulse

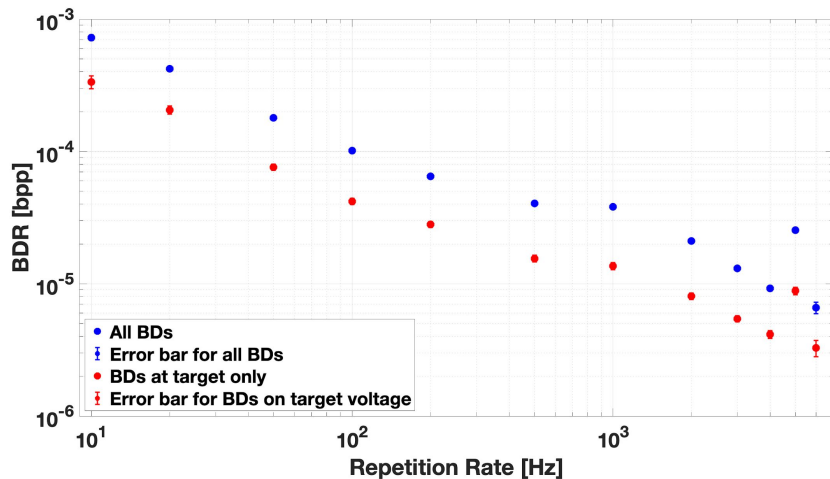


# Effect of the repetition rate

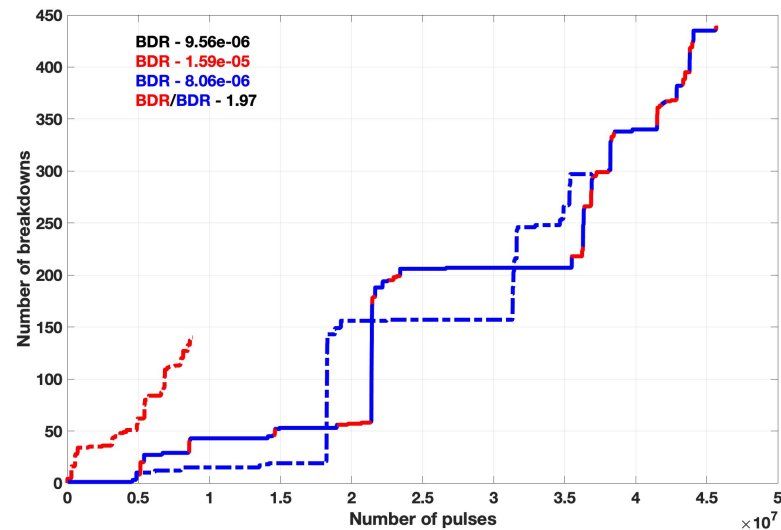
Measurements:  
Iaroslava Profatilova



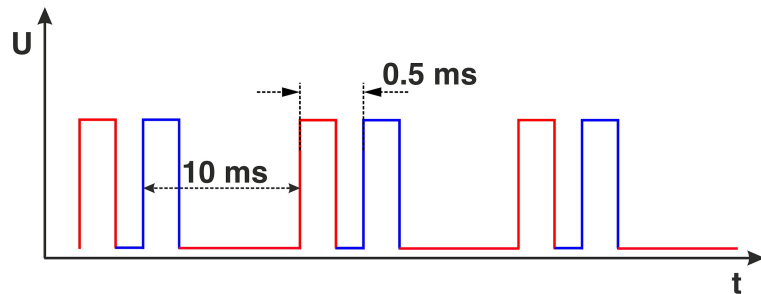
1.



2.



3.



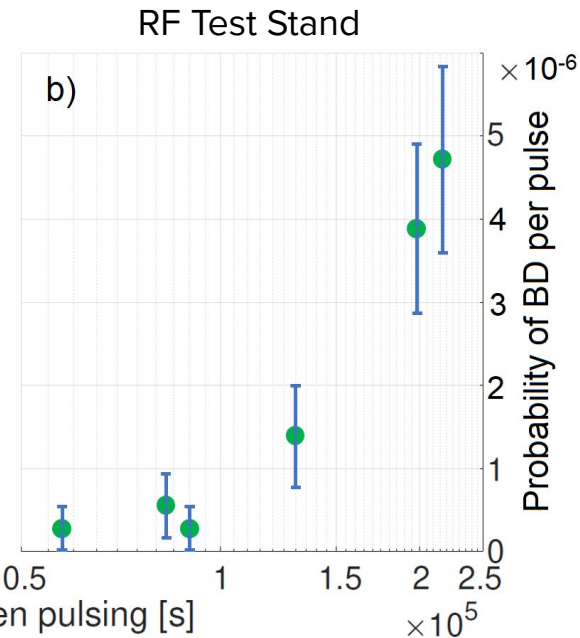
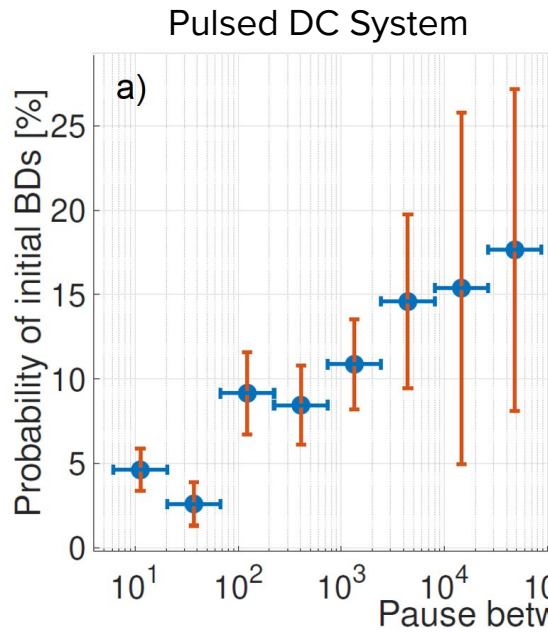
E [MV/m]	Pause [ms]	BDs	BDR [bpp]	Ratio
62	10	197	$2.30 \times 10^{-5}$	1.63
	0.5	121	$1.41 \times 10^{-5}$	
61	10	116	$9.30 \times 10^{-6}$	1.14
	0.5	121	$8.18 \times 10^{-6}$	
62	10	57	$8.05 \times 10^{-6}$	1.46
	0.5	39	$5.51 \times 10^{-6}$	



# Effect of a longer pause between measurements



- Previously qualitatively noticed that any pause in pulsing increases BD susceptibility
  - Both with DC and RF
  - Even when the system has been under UHV conditions
- => Needed to be measured quantitatively
  - Results both from DC and RF



- Increase in the values after  $\sim 100$  s and  $\sim 10^5$  pulses
  - Roughly the time of a monolayer formation

RF measurements:  
Lee Millar

# A longer pause increases BD susceptibility



- Several different experiments agree
  - Time scales from 0.5 ms to 28 h
- Best ramping scenario was the one with no pauses
- Each replate measurement shows a higher BDR after a longer idle time
- Initial BD probability increases with a longer pause between the measurements
- BDs after pauses linked to secondary BDs
  - I.e. events right after other BDs
  - Backed by the two-term exponential model fitted on the BD probability PDF
- => Secondary BDs mainly caused by surface impurities attaching on Cu surface from vacuum?
- However, the effect saturates at some point and is cleaned quickly with pulses and BDs

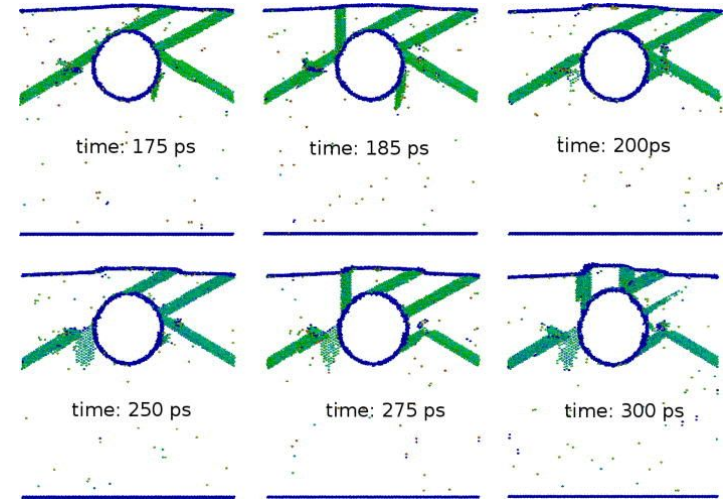
# He irradiation of Cu electrodes

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# The hypothesis linking He irradiation to BD generation

- He ions permeate the Cu surface, forming voids in the subsurface region ( $< 300$  nm)
- These voids act as nucleation sites for dislocations
- Dislocations, moving under stress caused by the electric pulsing, migrate to the surface and cause deformations
- Higher electric field near the deformation spots nucleate BDs

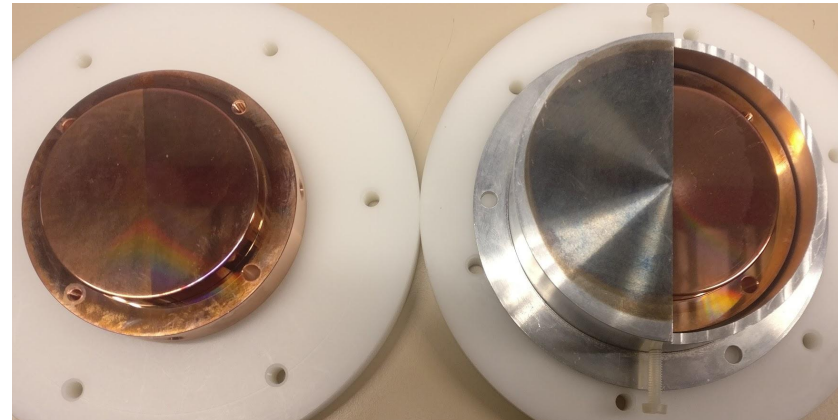


Pohjonen, A. S., et al. "Dislocation nucleation from near surface void under static tensile stress in Cu." *Journal of Applied Physics* 110.2 (2011): 023509.



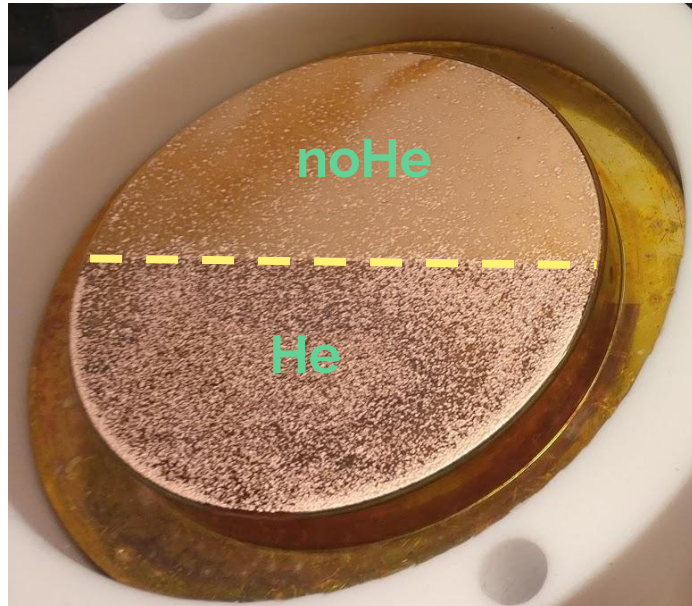
# He implantation - 2+1 pairs of electrodes

- Irradiation of two pairs in 2015 (Soft Cu)
  - He<sup>+</sup> with 30 keV
  - Fluence  $6.7 \times 10^{16}$  He/cm<sup>2</sup> (around 5 at.%)
  - Vacancy clusters confirmed up to 300 nm from the surface (PAS) close to the maximum depth of He ions (ERDA & SRIM)
- Another irradiation in 2018 (1 pair of Hard Cu)
  - Same parameters as in 2015
  - ERDA measurements after irradiation





# First results: He makes a difference



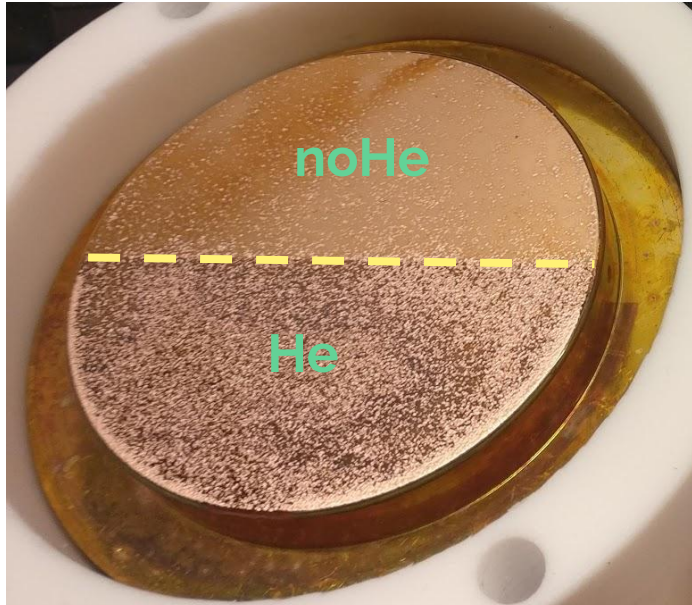
**Cathode**



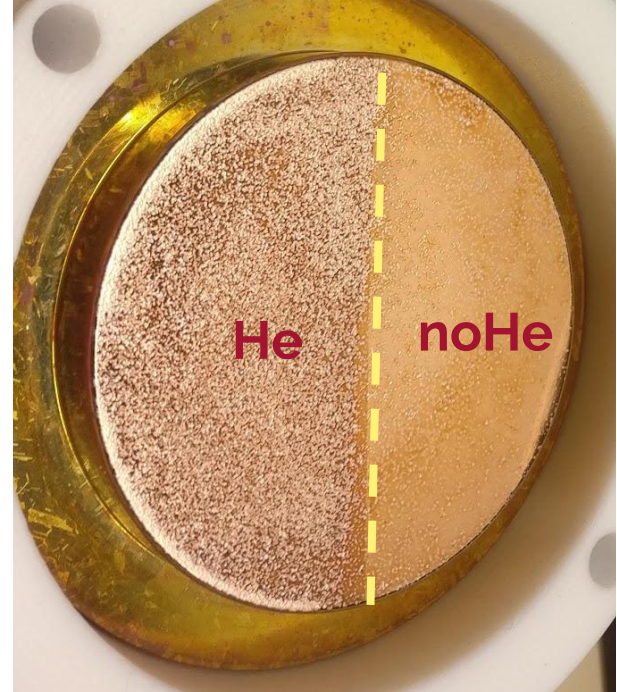
**Anode**



# Twisting the electrodes



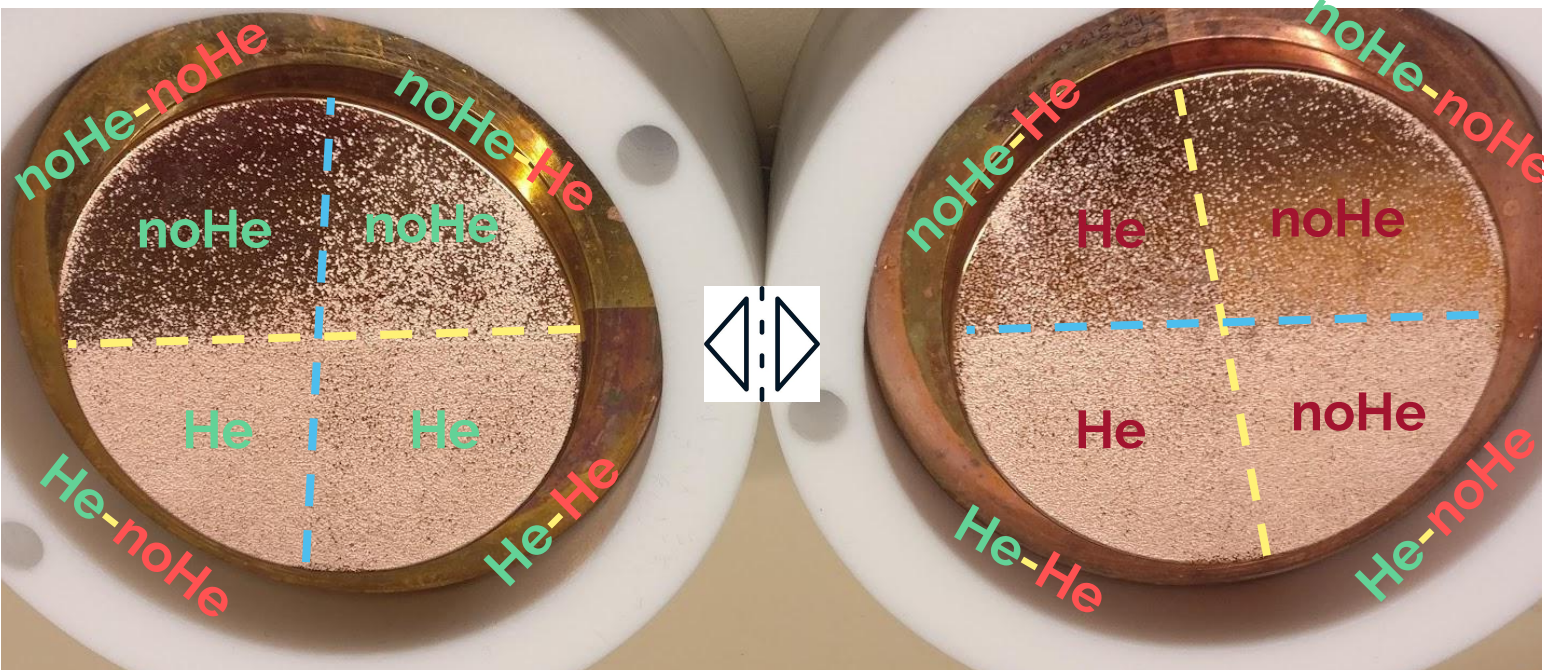
**Cathode**



**Anode**



# Twisting the electrodes shows BDs initiating from Cathode



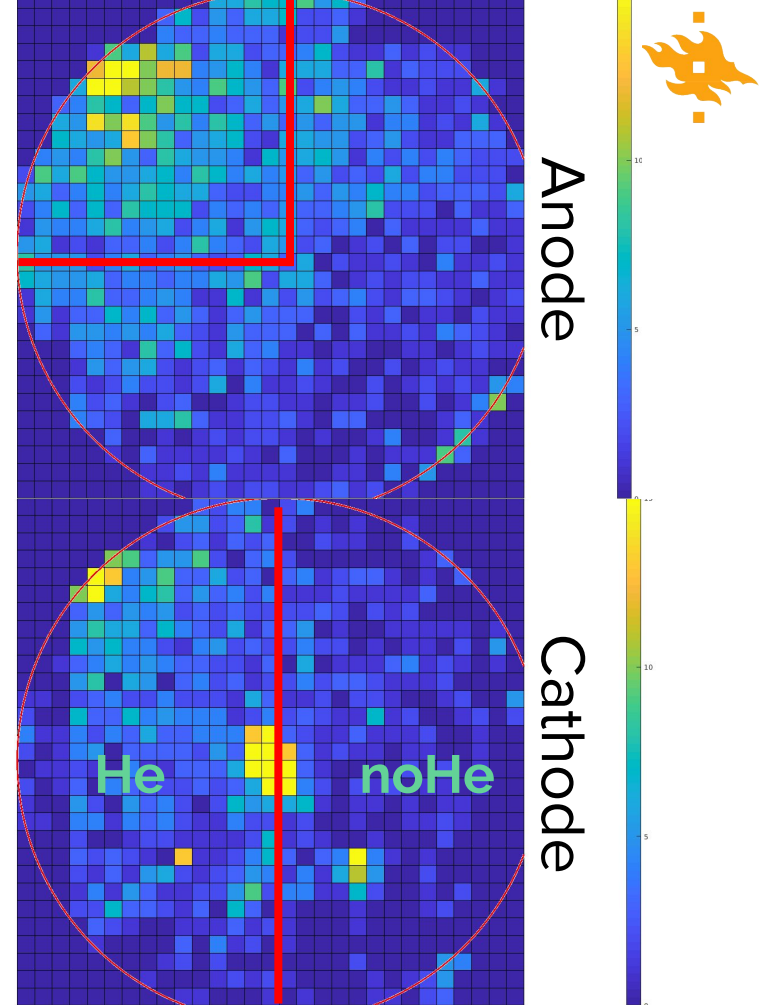
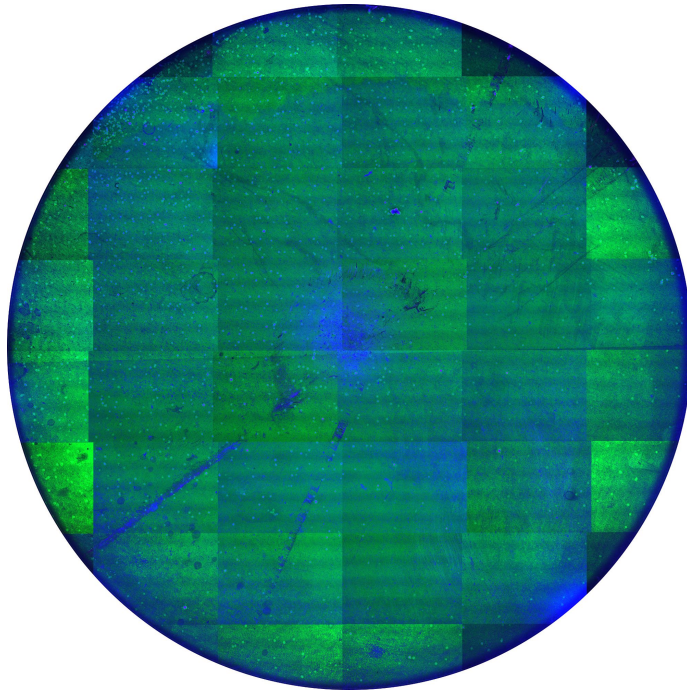
Cathode

Anode



# Similar results on Hard Cu He

- Controlled amount of 3000 BDs
- Difference between halves not so huge, but still observable

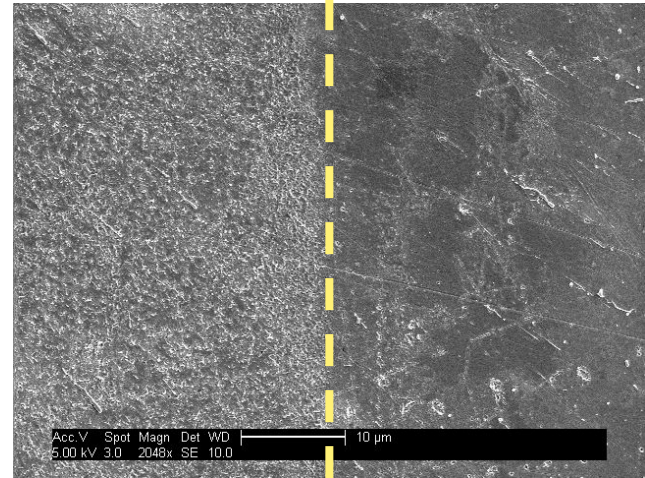
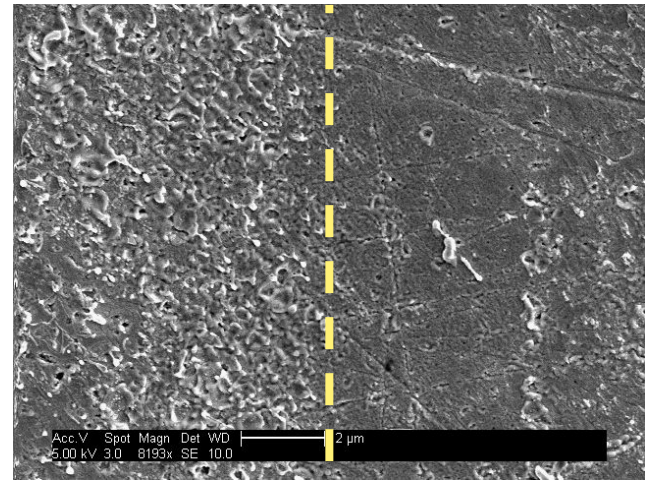


# Can we trust the results?

- Closer analysis shows that the He irradiation also modifies the surface
  - Increased surface roughness
  - Increased amounts of carbon
- Not clear yet, whether the voids are fully responsible for the increased amount of BDs

SEM images:  
Yinon Ashkenazy,  
Inna Popov &  
Ayelet Yashar

He irradiated



Non-irradiated



# Ongoing experiments: Plasma cleaning

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# Conclusions

- Pause between pulses affects BD probability
- Secondary BDs linked to surface impurities
- Surface impurities rapidly cleaned by pulses & BDs
- He irradiation leads to higher number of BDs
  - Reason not fully clear

Thank you  
for your attention!





# Cleaning the Cu surfaces in-situ with plasma

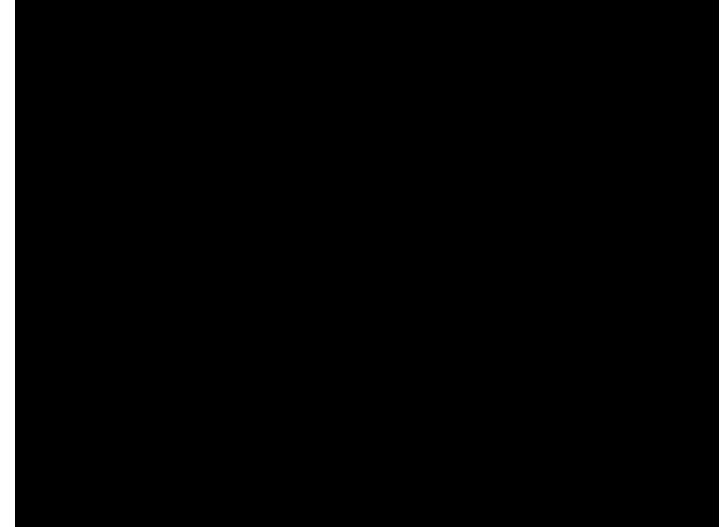
- **Idea**

“Micro sandblasting” the cathode surface with Ar<sup>+</sup> ions to get rid of surface impurities

- + Can be done in vacuum
- + Minimal damage to surface
- + HV equipment already there

- **Challenges**

- Need to use also other gases than Ar?
- Difficult to find the optimal parameters
  - Pressure, voltage, current, time
- Methods to study effects on the Cu surface



Video:  
Aarre Kilpeläinen